

Takhee Lee

List of Publications by Year in descending order

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363
papers

16,518
citations

14655

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docs citations

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times ranked

18226
citing authors

#	ARTICLE	IF	CITATIONS
1	Resistive Switching by Percolative Conducting Filaments in Organometal Perovskite Unipolar Memory Devices Analyzed Using Current Noise Spectra. <i>Advanced Functional Materials</i> , 2022, 32, 2107727.	14.9	8
2	Mark A. Reed (1955–2021). <i>Nature Nanotechnology</i> , 2022, , .	31.5	0
3	Tailoring the Electrical Characteristics of MoS ₂ FETs through Controllable Surface Charge Transfer Doping Using Selective Inkjet Printing. <i>ACS Nano</i> , 2022, 16, 6215-6223.	14.6	11
4	Channel-Length-Modulated Avalanche Multiplication in Ambipolar WSe ₂ Field-Effect Transistors. <i>ACS Nano</i> , 2022, 16, 5376-5383.	14.6	9
5	Photo-Responsive Molecular Junctions Activated by Perovskite/Graphene Heterostructure Electrode. <i>Advanced Optical Materials</i> , 2022, 10, .	7.3	4
6	Enhanced Thermoelectric Power Factor in Carrier-Type-Controlled Platinum Diselenide Nanosheets by Molecular Charge-Transfer Doping. <i>Small</i> , 2022, , 2200818.	10.0	1
7	Highly Integrated, Wearable Carbon-Nanotube-Yarn-Based Thermoelectric Generators Achieved by Selective Inkjet-Printed Chemical Doping. <i>Advanced Energy Materials</i> , 2022, 12, .	19.5	19
8	Stretchable hybrid electronics: combining rigid electronic devices with stretchable interconnects into high-performance on-skin electronics. <i>Journal of Information Display</i> , 2022, 23, 163-184.	4.0	17
9	Recent progress in strain-engineered elastic platforms for stretchable thin-film devices. <i>Materials Horizons</i> , 2022, 9, 2053-2075.	12.2	16
10	Integration of multiple electronic components on a microfibre towards an emerging electronic textile platform. <i>Nature Communications</i> , 2022, 13, .	12.8	27
11	Crystallinity-dependent device characteristics of polycrystalline 2D n = 4 Ruddlesden-Popper perovskite photodetectors. <i>Nanotechnology</i> , 2021, 32, 185203.	2.6	10
12	Tailored Design-of-Experiments Approach for Device Performance Prediction and Optimization of Flash-Evaporated Organic-Inorganic Halide Perovskite-Based Photodetectors. <i>Advanced Materials Technologies</i> , 2021, 6, 2001131.	5.8	5
13	Printed carbon electronics get recycled. <i>Nature Electronics</i> , 2021, 4, 241-242.	26.0	3
14	Perovskite Photodetector Devices: Tailored Design-of-Experiments Approach for Device Performance Prediction and Optimization of Flash-Evaporated Organic-Inorganic Halide Perovskite-Based Photodetectors (Adv. Mater. Technol. 5/2021). <i>Advanced Materials Technologies</i> , 2021, 6, 2170029.	5.8	0
15	Reversible Rectification of Microscale Ferroelectric Junctions Employing Liquid Metal Electrodes. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 29885-29893.	8.0	6
16	Temperature-Dependent Low-Frequency Noise Analysis of ZnO Nanowire Field-Effect Transistors. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 3532-3536.	3.0	5
17	Ultrasensitive Photodetection in MoS ₂ Avalanche Phototransistors. <i>Advanced Science</i> , 2021, 8, e2102437.	11.2	34
18	In-situ control of on-chip angstrom gaps, atomic switches, and molecular junctions by light irradiation. <i>Nano Today</i> , 2021, 39, 101226.	11.9	16

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19	Inkjet-Printing-Based Density Profile Engineering of Single-Walled Carbon Nanotube Networks for Conformable High-On/Off-Performance Thin-Film Transistors. <i>ACS Applied Materials & Interfaces</i> , 2021, 13, 43163-43173.	8.0	10
20	Molecular Dopant-Dependent Charge Transport in Surface-Charge-Transfer-Doped Tungsten Diselenide Field Effect Transistors. <i>Advanced Materials</i> , 2021, 33, e2101598.	21.0	20
21	Hierarchical Porous Film with Layer-by-Layer Assembly of 2D Copper Nanosheets for Ultimate Electromagnetic Interference Shielding. <i>ACS Nano</i> , 2021, 15, 829-839.	14.6	85
22	Layer-by-Layer Structural Identification of 2D Ruddlesden-Popper Hybrid Lead Iodide Perovskites by Solid-State NMR Spectroscopy. <i>Chemistry of Materials</i> , 2021, 33, 370-377.	6.7	44
23	Introduction to Molecular Interface Engineering of Transition Metal Dichalcogenide-based Devices. , 2021, , 43-91.		0
24	Proton irradiation effects on mechanochemically synthesized and flash-evaporated hybrid organic-inorganic lead halide perovskites. <i>Nanotechnology</i> , 2021, 33, .	2.6	2
25	Large-area molecular monolayer-based electronic junctions with transferred top electrodes. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SD0803.	1.5	2
26	Towards flexible CMOS circuits. <i>Nature Nanotechnology</i> , 2020, 15, 11-12.	31.5	16
27	Stretchable strain-tolerant soft printed circuit board: a systematic approach for the design rules of stretchable interconnects. <i>Journal of Information Display</i> , 2020, 21, 41-47.	4.0	14
28	High-performance compliant thermoelectric generators with magnetically self-assembled soft heat conductors for self-powered wearable electronics. <i>Nature Communications</i> , 2020, 11, 5948.	12.8	169
29	Crystal Size Effect on Carrier Transport of Microscale Perovskite Junctions via Soft Contact. <i>Nano Letters</i> , 2020, 20, 8640-8646.	9.1	18
30	Controllable deposition of organic metal halide perovskite films with wafer-scale uniformity by single source flash evaporation. <i>Scientific Reports</i> , 2020, 10, 18781.	3.3	6
31	Enhanced Output Performance of All-Solution-Processed Organic Thermoelectrics: Spray Printing and Interface Engineering. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 26250-26257.	8.0	10
32	Solution-Processed Transparent Superhydrophobic Protection Layers for Enhancing the Device Reliability of Flexible Organic Optoelectronics. <i>Advanced Materials Technologies</i> , 2020, 5, 2000449.	5.8	3
33	Tunable rectification in a molecular heterojunction with two-dimensional semiconductors. <i>Nature Communications</i> , 2020, 11, 1412.	12.8	19
34	All-Solid-State Organic Schmitt Trigger Implemented by Twin Two-In-One Ferroelectric Memory Transistors. <i>Advanced Electronic Materials</i> , 2020, 6, 1901263.	5.1	5
35	Highly Stable Contact Doping in Organic Field Effect Transistors by Dopant-Blockade Method. <i>Advanced Functional Materials</i> , 2020, 30, 2000058.	14.9	30
36	Electrical Characteristics of Molecular Junctions Fabricated by Inverted Self-Assembled Monolayer Method. <i>Journal of Nanoscience and Nanotechnology</i> , 2020, 20, 4648-4651.	0.9	0

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37	Enhanced Photoresponse of Mos 2 Photodetectors by a Laterally Aligned SiO 2 Nanoribbon Array Substrate. ChemNanoMat, 2019, 5, 1272-1279.	2.8	2
38	Highly uniform monolayer graphene synthesis via a facile pretreatment of copper catalyst substrates using an ammonium persulfate solution. RSC Advances, 2019, 9, 20871-20878.	3.6	6
39	Recent Advances in Interface Engineering of Transition-Metal Dichalcogenides with Organic Molecules and Polymers. ACS Nano, 2019, 13, 9713-9734.	14.6	72
40	Intrinsic Optoelectronic Characteristics of MoS ₂ Phototransistors via a Fully Transparent van der Waals Heterostructure. ACS Nano, 2019, 13, 9638-9646.	14.6	43
41	Dose-dependent effect of proton irradiation on electrical properties of WSe ₂ ambipolar field effect transistors. Nanoscale, 2019, 11, 13961-13967.	5.6	5
42	Fabrication of a MoS ₂ /Graphene Nanoribbon Heterojunction Network for Improved Thermoelectric Properties. Advanced Materials Interfaces, 2019, 6, 1901333.	3.7	26
43	Nano as a Rosetta Stone: The Global Roles and Opportunities for Nanoscience and Nanotechnology. ACS Nano, 2019, 13, 10853-10855.	14.6	16
44	Enhanced Charge Injection Properties of Organic Field-Effect Transistor by Molecular Implantation Doping. Advanced Materials, 2019, 31, e1806697.	21.0	60
45	Organic Field-Effect Transistors: Enhanced Charge Injection Properties of Organic Field-Effect Transistor by Molecular Implantation Doping (Adv. Mater. 10/2019). Advanced Materials, 2019, 31, 1970073.	21.0	2
46	Recent Progress in Inkjet-Printed Thin-Film Transistors. Advanced Science, 2019, 6, 1801445.	11.2	187
47	Atomic switches of metallic point contacts by plasmonic heating. Light: Science and Applications, 2019, 8, 34.	16.6	26
48	High-Performance Solution-Processed Organo-Metal Halide Perovskite Unipolar Resistive Memory Devices in a Cross-Bar Array Structure. Advanced Materials, 2019, 31, e1804841.	21.0	100
49	Unidirectional Real-Time Photoswitching of Diarylethene Molecular Monolayer Junctions with Multilayer Graphene Electrodes. ACS Applied Materials & Interfaces, 2019, 11, 11645-11653.	8.0	23
50	Trapped charge modulation at the MoS ₂ /SiO ₂ interface by a lateral electric field in MoS ₂ field-effect transistors. Nano Futures, 2019, 3, 011002.	2.2	13
51	Effect of Facile p-Doping on Electrical and Optoelectronic Characteristics of Ambipolar WSe2 Field-Effect Transistors. Nanoscale Research Letters, 2019, 14, 313.	5.7	9
52	Electrical modulation of a photonic crystal band-edge laser with a graphene monolayer. Nanoscale, 2018, 10, 8496-8502.	5.6	7
53	Contact-Engineered Electrical Properties of MoS ₂ Field-Effect Transistors via Selectively Deposited Thiol-Molecules. Advanced Materials, 2018, 30, e1705540.	21.0	56
54	An on-chip hybrid plasmonic light steering concentrator with ~49% coupling efficiency. Nanoscale, 2018, 10, 5097-5104.	5.6	9

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55	Peltier cooling at molecular scale. <i>Nature Nanotechnology</i> , 2018, 13, 97-99.	31.5	5
56	Field-Effect Transistors: Contact-Engineered Electrical Properties of MoS ₂ Field-Effect Transistors via Selectively Deposited Thiol-Molecules (<i>Adv. Mater.</i> 18/2018). <i>Advanced Materials</i> , 2018, 30, 1870129.	21.0	1
57	Shaping the Atomic-Scale Geometries of Electrodes to Control Optical and Electrical Performance of Molecular Devices. <i>Small</i> , 2018, 14, e1703815.	10.0	28
58	Highly Reliable Superhydrophobic Protection for Organic Field-Effect Transistors by Fluoroalkylsilane-Coated TiO ₂ Nanoparticles. <i>ACS Nano</i> , 2018, 12, 11062-11069.	14.6	32
59	Nanoscale enhancement of photoconductivity by localized charge traps in the grain structures of monolayer MoS ₂ . <i>Scientific Reports</i> , 2018, 8, 15822.	3.3	11
60	Molecular Orbital Gating Surface-Enhanced Raman Scattering. <i>ACS Nano</i> , 2018, 12, 11229-11235.	14.6	27
61	Effects of Electron Beam Irradiation and Thiol Molecule Treatment on the Properties of MoS ₂ Field Effect Transistors. <i>Journal of the Korean Physical Society</i> , 2018, 72, 1203-1208.	0.7	7
62	Molecular Devices: Shaping the Atomic-Scale Geometries of Electrodes to Control Optical and Electrical Performance of Molecular Devices (<i>Small</i> 15/2018). <i>Small</i> , 2018, 14, 1870066.	10.0	3
63	Near-Ultraviolet Structural Colors Generated by Aluminum Nanodisk Array for Bright Image Printing. <i>Advanced Optical Materials</i> , 2018, 6, 1800231.	7.3	9
64	Electronic skins for soft, compact, reversible assembly of wirelessly activated fully soft robots. <i>Science Robotics</i> , 2018, 3, .	17.6	176
65	Two-Dimensional Thickness-Dependent Avalanche Breakdown Phenomena in MoS ₂ Field-Effect Transistors under High Electric Fields. <i>ACS Nano</i> , 2018, 12, 7109-7116.	14.6	43
66	Correlational Effects of the Molecular-Tilt Configuration and the Intermolecular van der Waals Interaction on the Charge Transport in the Molecular Junction. <i>Nano Letters</i> , 2018, 18, 4322-4330.	9.1	14
67	Investigation of Time-Dependent Resistive Switching Behaviors of Unipolar Nonvolatile Organic Memory Devices. <i>Advanced Functional Materials</i> , 2018, 28, 1801162.	14.9	34
68	Single-molecule devices reveal step-by-step dynamics of hydrogen bonds. <i>Science China Chemistry</i> , 2018, 61, 639-640.	8.2	0
69	Miniaturization and Integration of Organic Resistive Memory Devices. <i>Journal of the Korean Physical Society</i> , 2018, 73, 479-487.	0.7	1
70	Resistive Switching Memory: Investigation of Time-Dependent Resistive Switching Behaviors of Unipolar Nonvolatile Organic Memory Devices (<i>Adv. Funct. Mater.</i> 35/2018). <i>Advanced Functional Materials</i> , 2018, 28, 1870249.	14.9	4
71	One-Step Interface Engineering for All-Inkjet-Printed, All-Organic Components in Transparent, Flexible Transistors and Inverters: Polymer Binding. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 8819-8829.	8.0	34
72	Attachable and flexible aluminum oxide resistive non-volatile memory arrays fabricated on tape as the substrate. <i>Nanotechnology</i> , 2017, 28, 135201.	2.6	5

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73	Analysis of the interface characteristics of CVD-grown monolayer MoS ₂ by noise measurements. <i>Nanotechnology</i> , 2017, 28, 145702.	2.6	14
74	Nanoscience and Nanotechnology Cross Borders. <i>ACS Nano</i> , 2017, 11, 1123-1126.	14.6	4
75	Fabrication of Millimeter-Long Carbon Tubular Nanostructures Using the Self-Rolling Process Inherent in Elastic Protein Layers. <i>Advanced Materials</i> , 2017, 29, 1701732.	21.0	5
76	Analysis of noise generation and electric conduction at grain boundaries in CVD-grown MoS ₂ field effect transistors. <i>Nanotechnology</i> , 2017, 28, 47LT01.	2.6	9
77	Comparative study for electrical transport characteristics of self-assembled monolayers formed by benzenethiol, cyclohexanethiol, and adamantanethiol. <i>Current Applied Physics</i> , 2017, 17, 1459-1464.	2.4	8
78	Transparent Large-Area MoS ₂ Phototransistors with Inkjet-Printed Components on Flexible Platforms. <i>ACS Nano</i> , 2017, 11, 10273-10280.	14.6	72
79	High-Yield Functional Molecular Electronic Devices. <i>ACS Nano</i> , 2017, 11, 6511-6548.	14.6	136
80	Solution-Processed Complementary Resistive Switching Arrays for Associative Memory. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 4310-4316.	3.0	19
81	Interface-Engineered Charge-Transport Properties in Benzenedithiol Molecular Electronic Junctions via Chemically p-Doped Graphene Electrodes. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 42043-42049.	8.0	10
82	Electronic noise analyses on organic electronic devices. <i>Journal of Materials Chemistry C</i> , 2017, 5, 7123-7141.	5.5	16
83	A High-Speed Inkjet-Printed Microelectromechanical Relay With a Mechanically Enhanced Double-Clamped Channel-Beam. <i>Journal of Microelectromechanical Systems</i> , 2017, 26, 95-101.	2.5	7
84	Realization of an atomically flat BaSnO ₃ (001) substrate with SnO ₂ termination. <i>Applied Physics Letters</i> , 2017, 111, .	3.3	11
85	Transparent p-n-BaSnO ₃ heterojunctions with a high rectification ratio. <i>Journal of Physics Condensed Matter</i> , 2017, 29, 384004.	1.8	19
86	Efficient Surface Treatment to Improve Contact Properties of Inkjet-Printed Short-Channel Organic Thin-Film Transistors. <i>Journal of Nanoscience and Nanotechnology</i> , 2017, 17, 5718-5721.	0.9	9
87	Tailoring the electrical properties of MoS ₂ field effect transistors by depositing Au nanoparticles and alkanethiol molecules. <i>Journal of Physics Condensed Matter</i> , 2016, 28, 184003.	1.8	1
88	The development of fluoros photolithographic materials and their applications to achieve flexible organic electronic devices. <i>Flexible and Printed Electronics</i> , 2016, 1, 023001.	2.7	15
89	71-2: Invited Paper: Printed Transistors and MEMS for Large-Area Electronics. <i>Digest of Technical Papers SID International Symposium</i> , 2016, 47, 956-959.	0.3	1
90	Improved photoswitching response times of MoS ₂ field-effect transistors by stacking p-type copper phthalocyanine layer. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	29

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91	Fully inkjet-printed short-channel organic thin-film transistors and inverter arrays on flexible substrates. Flexible and Printed Electronics, 2016, 1, 045003.	2.7	15
92	Enhanced electron mobility in epitaxial (Ba,Lu)SnO ₃ films on BaSnO ₃ (001) substrates. Applied Physics Letters, 2016, 108, .	3.3	69
93	Characterization of PI:PCBM organic nonvolatile resistive memory devices under thermal stress. Organic Electronics, 2016, 33, 48-54.	2.6	22
94	Catalyst-free bottom-up growth of graphene nanofeatures along with molecular templates on dielectric substrates. Nanoscale, 2016, 8, 17022-17029.	5.6	20
95	Single-Atom Switches and Single-Atom Gaps Using Stretched Metal Nanowires. ACS Nano, 2016, 10, 9695-9702.	14.6	43
96	Large scale MoS ₂ nanosheet logic circuits integrated by photolithography on glass. 2D Materials, 2016, 3, 044001.	4.4	26
97	Laser direct writing and inkjet printing for a sub-200 nm channel length MoS ₂ transistor with high-resolution electrodes. Nanotechnology, 2016, 27, 405301.	2.6	14
98	Trap-mediated electronic transport properties of gate-tunable pentacene/MoS ₂ p-n heterojunction diodes. Scientific Reports, 2016, 6, 36775.	3.3	54
99	Origin of multi-level switching and telegraphic noise in organic nanocomposite memory devices. Scientific Reports, 2016, 6, 33967.	3.3	21
100	Non-volatile aluminum oxide resistive memory devices on a wrapping paper substrate. Flexible and Printed Electronics, 2016, 1, 034001.	2.7	4
101	Gate-dependent asymmetric transport characteristics in pentacene barristors with graphene electrodes. Nanotechnology, 2016, 27, 475201.	2.6	3
102	Integration of Flexible and Microscale Organic Nonvolatile Resistive Memory Devices Using Orthogonal Photolithography. Journal of Nanoscience and Nanotechnology, 2016, 16, 6350-6354.	0.9	3
103	Fully Inkjet-Printed Stress-Tolerant Microelectromechanical Reed Relays for Large-Area Electronics. Advanced Electronic Materials, 2016, 2, 1500482.	5.1	12
104	Electrical Properties of Synthesized Large-Area MoS ₂ Field-Effect Transistors Fabricated with Inkjet-Printed Contacts. ACS Nano, 2016, 10, 2819-2826.	14.6	64
105	P-type CuO and Cu ₂ O transistors derived from a sol-gel copper (II) acetate monohydrate precursor. Thin Solid Films, 2016, 600, 157-161.	1.8	72
106	Molecular-Scale Electronics: From Concept to Function. Chemical Reviews, 2016, 116, 4318-4440.	47.7	1,014
107	Statistical investigation of the length-dependent deviations in the electrical characteristics of molecular electronic junctions fabricated using the direct metal transfer method. Journal of Physics Condensed Matter, 2016, 28, 094003.	1.8	7
108	An In-Depth Study of Redox-Induced Conformational Changes in Charge Transport Characteristics of a Ferrocene-Alkanethiolate Molecular Electronic Junction: Temperature-Dependent Transition Voltage Spectroscopy Analysis. Journal of Physical Chemistry C, 2016, 120, 3564-3572.	3.1	20

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109	A robust, gravure-printed, silver nanowire/metal oxide hybrid electrode for high-throughput patterned transparent conductors. <i>Journal of Materials Chemistry C</i> , 2016, 4, 3248-3255.	5.5	60
110	Electrical characterization of benzenedithiolate molecular electronic devices with graphene electrodes on rigid and flexible substrates. <i>Nanotechnology</i> , 2016, 27, 145301.	2.6	12
111	Introduction to research of atomically thin MoS ₂ and its electrical properties. <i>Vacuum Magazine</i> , 2016, 3, 9-15.	0.0	0
112	Domain Aligned Growth of Molybdenum Disulfide on Various Substrates by Chemical Vapor Deposition. <i>Science of Advanced Materials</i> , 2016, 8, 1683-1687.	0.7	0
113	Electrical Characteristics of Benzenedithiol versus Methylbenzenethiol Self-Assembled Monolayers in Multilayer Graphene-Electrode Molecular Junctions. <i>Journal of Nanoscience and Nanotechnology</i> , 2016, 16, 8565-8568.	0.9	2
114	Statistical Analysis of Electrical Properties of Octanemonthiol versus Octanedithiol in PEDOT:PSS-Electrode Molecular Junctions. <i>Journal of Nanoscience and Nanotechnology</i> , 2015, 15, 5937-5941.	0.9	1
115	Reversible Switching Phenomenon in Diarylethene Molecular Devices with Reduced Graphene Oxide Electrodes on Flexible Substrates. <i>Advanced Functional Materials</i> , 2015, 25, 5918-5923.	14.9	39
116	Energy Consumption Estimation of Organic Nonvolatile Memory Devices on a Flexible Plastic Substrate. <i>Advanced Electronic Materials</i> , 2015, 1, 1500186.	5.1	12
117	Interface effect in pentacene field-effect transistors from high energy proton beam irradiation. <i>Organic Electronics</i> , 2015, 27, 240-246.	2.6	7
118	1/f Noise Scaling Analysis in Unipolar-Type Organic Nanocomposite Resistive Memory. <i>ACS Nano</i> , 2015, 9, 7697-7703.	14.6	24
119	Graphene/Pentacene Barristor with Ion-Gel Gate Dielectric: Flexible Ambipolar Transistor with High Mobility and On/Off Ratio. <i>ACS Nano</i> , 2015, 9, 7515-7522.	14.6	46
120	Facile anionic synthesis of a well-controlled thermally cross-linkable block copolymer for polymer-based resistive memory device applications. <i>Polymer Chemistry</i> , 2015, 6, 4264-4270.	3.9	13
121	Vertically stacked microscale organic nonvolatile memory devices toward three-dimensional high integration. <i>Organic Electronics</i> , 2015, 21, 198-202.	2.6	10
122	Hydrogen plasma-mediated modification of the electrical transport properties of ZnO nanowire field effect transistors. <i>Nanotechnology</i> , 2015, 26, 125202.	2.6	11
123	High-Performance Inkjet-Printed Four-Terminal Microelectromechanical Relays and Inverters. <i>Nano Letters</i> , 2015, 15, 3261-3266.	9.1	23
124	Investigation of inelastic electron tunneling spectra of metal-molecule-metal junctions fabricated using direct metal transfer method. <i>Applied Physics Letters</i> , 2015, 106, .	3.3	18
125	Electrical and Optical Characterization of MoS ₂ with Sulfur Vacancy Passivation by Treatment with Alkanethiol Molecules. <i>ACS Nano</i> , 2015, 9, 8044-8053.	14.6	185
126	Enhancement of photodetection characteristics of MoS ₂ field effect transistors using surface treatment with copper phthalocyanine. <i>Nanoscale</i> , 2015, 7, 18780-18788.	5.6	101

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127	A new approach for high-yield metal–molecule–metal junctions by direct metal transfer method. <i>Nanotechnology</i> , 2015, 26, 025601.	2.6	17
128	4K-bit and microlithographic integration of organic nonvolatile resistive memory devices. <i>Organic Electronics</i> , 2015, 17, 192-197.	2.6	16
129	Exploitation of the coffee-ring effect to realize mechanically enhanced inkjet-printed microelectromechanical relays with U-bar-shaped cantilevers. <i>Applied Physics Letters</i> , 2014, 105, .	3.3	17
130	Origin of discrete current fluctuations in a single molecule junction. <i>Nanoscale</i> , 2014, 6, 13396-13401.	5.6	33
131	Well-Defined Block Copolymers with Triphenylamine and Isocyanate Moieties Synthesized via Living Anionic Polymerization for Polymer-Based Resistive Memory Applications: Effect of Morphological Structures on Nonvolatile Memory Performances. <i>Macromolecules</i> , 2014, 47, 8625-8633.	4.8	11
132	Inkjet-printed stretchable single-walled carbon nanotube electrodes with excellent mechanical properties. <i>Applied Physics Letters</i> , 2014, 104, .	3.3	58
133	Flexible Molecular-Scale Electronic Devices Composed of Diarylethene Photoswitching Molecules. <i>Advanced Materials</i> , 2014, 26, 3968-3973.	21.0	72
134	Organic Electronics: Graphene–Conducting Polymer Hybrid Transparent Electrodes for Efficient Organic Optoelectronic Devices (<i>Adv. Funct. Mater.</i> 13/2014). <i>Advanced Functional Materials</i> , 2014, 24, 1960-1960.	14.9	1
135	Redox-Induced Asymmetric Electrical Characteristics of Ferrocene–Alkanethiolate Molecular Devices on Rigid and Flexible Substrates. <i>Advanced Functional Materials</i> , 2014, 24, 2472-2480.	14.9	68
136	The application of orthogonal photolithography to micro-scale organic field effect transistors and complementary inverters on flexible substrate. <i>Applied Physics Letters</i> , 2014, 104, 053301.	3.3	20
137	Analysis of surface states in ZnO nanowire field effect transistors. <i>Applied Surface Science</i> , 2014, 301, 2-8.	6.1	5
138	Graphene–Conducting Polymer Hybrid Transparent Electrodes for Efficient Organic Optoelectronic Devices. <i>Advanced Functional Materials</i> , 2014, 24, 1847-1856.	14.9	76
139	Molecular Electronics: Redox-Induced Asymmetric Electrical Characteristics of Ferrocene-Alkanethiolate Molecular Devices on Rigid and Flexible Substrates (<i>Adv. Funct. Mater.</i>) Tj ETQq1 1 0.784344 rgBT /Overlock		
140	Gate-bias stress-dependent photoconductive characteristics of multi-layer MoS ₂ field-effect transistors. <i>Nanotechnology</i> , 2014, 25, 155201.	2.6	42
141	Micro-scale twistable organic field effect transistors and complementary inverters fabricated by orthogonal photolithography on flexible polyimide substrate. <i>Organic Electronics</i> , 2014, 15, 2822-2829.	2.6	16
142	Irradiation Effects of High-Energy Proton Beams on MoS ₂ Field Effect Transistors. <i>ACS Nano</i> , 2014, 8, 2774-2781.	14.6	100
143	Facile anionic synthesis of well-defined block copolymers with pendent triphenylamine and ethynylpyridine for nonvolatile memory device applications with high performances. <i>Journal of Polymer Science Part A</i> , 2014, 52, 2625-2632.	2.3	11
144	Photoelectron Spectroscopic Imaging and Device Applications of Large-Area Patternable Single-Layer MoS ₂ Synthesized by Chemical Vapor Deposition. <i>ACS Nano</i> , 2014, 8, 4961-4968.	14.6	117

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145	Temperature Dependence of Electron Transport in ZnO Nanowire Field Effect Transistors. IEEE Transactions on Electron Devices, 2014, 61, 625-630.	3.0	3
146	Effect of molecular desorption on the electronic properties of self-assembled polarizable molecular monolayers. Journal of Colloid and Interface Science, 2014, 419, 39-45.	9.4	13
147	Inelastic electron tunneling spectroscopy of molecular transport junctions. Journal of the Korean Physical Society, 2014, 64, 1539-1544.	0.7	3
148	Study on the Origin of Amorphous Carbon Peaks on Graphene Films Synthesized on Nickel Catalysts. Journal of Nanoscience and Nanotechnology, 2014, 14, 4982-4987.	0.9	3
149	Mechanically Controllable Break Junctions for Molecular Electronics. Advanced Materials, 2013, 25, 4845-4867.	21.0	192
150	Three-Terminal Single-Molecule Junctions Formed by Mechanically Controllable Break Junctions with Side Gating. Nano Letters, 2013, 13, 2809-2813.	9.1	103
151	Graphene Films Show Stable Cell Attachment and Biocompatibility with Electrogenic Primary Cardiac Cells. Molecules and Cells, 2013, 36, 577-582.	2.6	36
152	Electric Stress-Induced Threshold Voltage Instability of Multilayer MoS ₂ Field Effect Transistors. ACS Nano, 2013, 7, 7751-7758.	14.6	190
153	Demonstration of Addressable Organic Resistive Memory Utilizing a PC-Interface Memory Cell Tester. IEEE Electron Device Letters, 2013, 34, 51-53.	3.9	10
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